

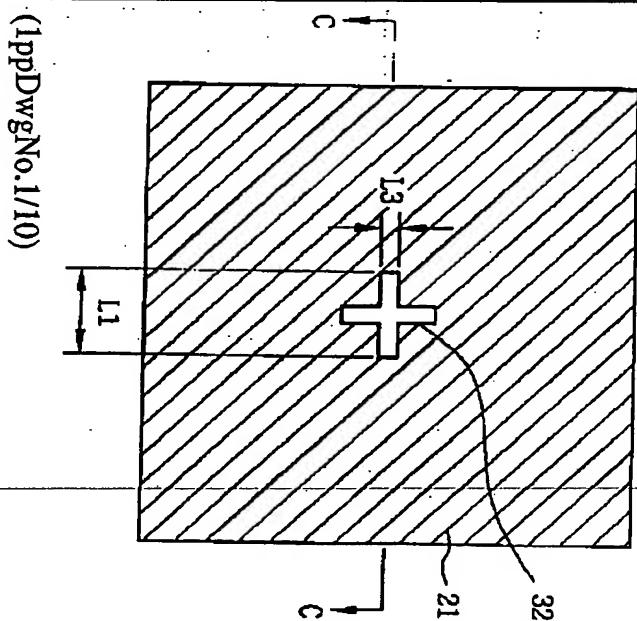
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SAMSUNG ELECTRONICS CO LTD *KR 2001107242-A
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Phase shift mask
C2002-101854
Addnl. Data: SON C J

NOVELTY

A phase shift mask is provided to enhance an integration rate of a semiconductor device by forming stably a margin of a photo process for forming a contact hole of a fine pattern.

DETAILED DESCRIPTION

A phase shift layer(21) is stacked on a whole face of a permeable quartz substrate. An aperture(32) of a cross shape is formed on a center portion of the phase shift layer(21). The aperture(32) is used for forming a contact hole. A width(L3) and a length(L1) of the aperture(32) can be optimized according to a size of the contact hole. A molybdenum silicide layer having transmissivity of 8 percent can be used as the phase shift layer(21). In order to improve a resolution, the transmissivity of the phase shift layer(21) is controlled according to a thickness of the phase shift layer(21).



(1ppDwgNo.1/10)